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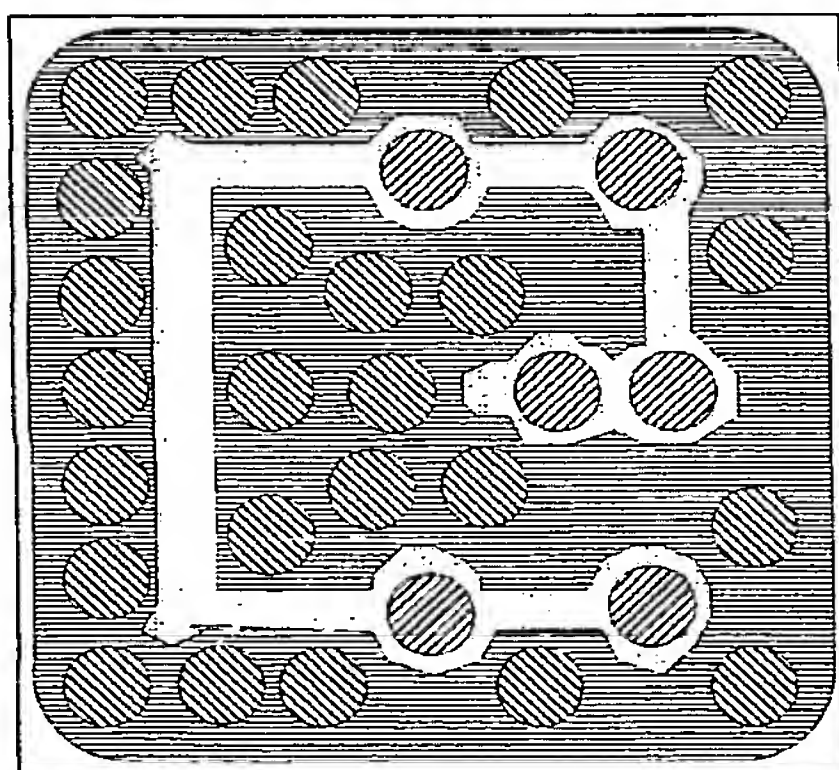
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(54) Title: OPTIMIZED CONTACT DESIGN FOR THERMOSONIC BONDING OF FLIP-CHIP DEVICES



A KEY

- B n-type bump area (320n)  
C p-type bump area (320p)  
D n-type trace corresponding to n-type contact (180n)  
E p-type trace corresponding to p-type contact (180p)

(57) Abstract: A light emitting device (A) includes a semiconductor die (100). The semiconductor die includes: an epitaxial structure (120) arranged on a substrate (160), the epitaxial structure forming an active light generating region (140) between a first layer (120n) on a first side of the active region and having a first conductivity type, and a second layer (120p) on a second side of the active region and having a second conductivity type, the second side of the active region being opposite the first side of the active region and the second conductivity type being different than the first conductivity type; a first contact (180n) in operative electrical communication with the active region via the first layer in the epitaxial structure, the first contact being arranged on a side of the epitaxial structure opposite the substrate; a second contact (180p) in operative electrical communication with the active region via the second layer in the epitaxial structure, the second contact being arranged on a side of the epitaxial structure opposite the substrate; a first contact trace corresponding to the first contact and defined at a surface thereof distal from the substrate, the first trace including at least one area designated for bonding (320n); and, a second contact trace corresponding to the second contact and defined at a surface thereof distal from the substrate, the second trace including at least one area (320p) designated for bonding. Suitably, the first contact trace is substantially enclosed within the second contact trace.

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